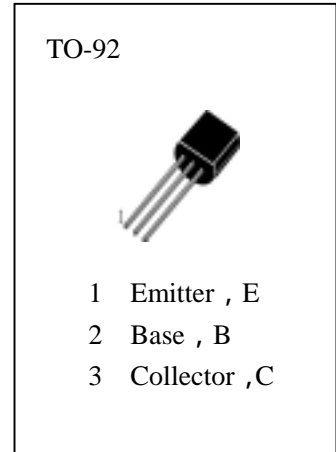




HIGH VOLTAGE TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (Ta=25)

- T_{stg}—Storage Temperature..... -55~150
- T_j—Junction Temperature.....150
- P_C—Collector Dissipation.....625mW
- V_{CBO}—Collector-Base Voltage.....-300V
- V_{CEO}—Collector-Emitter Voltage.....-300V
- V_{EBO}—Emitter-Base Voltage.....-5V
- I_C—Collector Current.....-500mA



ELECTRICAL CHARACTERISTICS (Ta=25)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	-300			V	I _C =-100 μ A, I _E =0
BVCEO	Collector-Emitter Breakdown Voltage	-300			V	I _C =-1mA, I _B =0
BVEBO	Emitter-Base Breakdown Voltage	-5			V	I _E =-100 μ A , I _C =0
ICBO	Collector Cut-off Current			-250	nA	V _{CB} =-200V, I _E =0
IEBO	Emitter-Base Cut-off Current			-100	nA	V _{EB} =-3V, I _C =0
ICES	Collector Cut-off Current			-100	nA	V _{CE} =-300V, V _{BE} =0
HFE (1)	DC Current Gain	25				V _{CE} =-10V, I _C =-1mA
HFE (2)		40				V _{CE} =-10V, I _C =-10mA
HFE (3)		50				V _{CE} =-10V, I _C =-30mA
VCE(sat1)	Collector- Emitter Saturation Voltage			-0.5	V	I _C =-20mA, I _B =-2mA
VCE(sat2)				-1	V	I _C =-60mA, I _B =-6mA
VBE(sat1)	Base-Emitter Saturation Voltage			-0.9	V	I _C =-20mA, I _B =-2mA
f _T	Current Gain-Bandwidth Product	50			MHZ	V _{CE} =-20V, I _C =-10mA F=100MHZ